

09/786338

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PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Tetsuhiro TANABE et al.

New U.S. PCT Appln. No. PCT/JP99/04903

Filed: March 8, 2001

Attorney Dkt. No.: 107400-00023

For: SEMICONDUCTOR LIGHT EMITTING DEVICE AND METHOD FOR
MANUFACTURING THE SAME

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

March 8, 2001

Sir:

Prior to initial examination of the application, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 4, 7, 8, 35, 38 and 53 as follows:

4. (Amended) The semiconductor light emitting device of claim 1, wherein
said active layer is made of $Cd_xZn_{1-x}O$ ($0 \leq x < 1$).

7. (Amended) The semiconductor light emitting device of claim 1 or 5,
wherein the substrate on which said cladding layers and said active layer are laminated
is one kind selected from the group consisting of GaN, Si having SiC formed thereon,
single crystal SiC, and sapphire.